NSN 5962-01-376-2200

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View Online at https://aerobasegroup.com/nsn/5962-01-376-2200

Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
5975-01-253-6144 junction box
Features Provided:
Programmed and bipolar and schottky and monolithic and w/enable and w/inhibit and high impedance and w/buffered output
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
14 input
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
190.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Capitance Rating Per Characteristic:
10.00 input picofarads and 15.00 output picofarads
Time Rating Per Chacteristic:
70.00 nanoseconds access
Memory Device Type:
Prom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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